DOCUMENT CHANGE REQUEST

DCR number 1091	Changes required for: General		Originator: Samuel Savin
Date: 2017/09/26	Date sent: 2017/06/05		Organisation: STMicroelectronics
Status: IMPLEMENTED			

Title:	TRANSISTORS, POWER, MOSFET, N-CHANNEL, RAD-HARD BASED ON TYPE STRH8N10		
Number:	5205/023	Issue:	4

Other documents affected:

Page:

11

Paragraph:

2.4.1 Room Temperature Electrical Measurements

Original wording:

See document an attachment.

Proposed wording:

See document an attachment.

Justification:

See document an attachment.

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Paragraph:

2.10.2

Original wording:

see published specification

Proposed wording:

The same change to Qgd limit (i.e. to be 4.3nC min / 6.5nC max) introduced in th is DCR shall also apply to the table in Para 2.10.2 (irradiation electrical measurements).

Justification:

Attachments:

dcr_strh8n10.pdf

Modifications:

The same change to Qgd limit (i.e. to be 4.3nC min / 6.5nC max) shall also apply to the table in Para 2.10.2 (irradiation electrical measurements).

Approval signature:

Date signed:

2017-09-26